

**VIETNAM NATIONAL UNIVERSITY HO CHI MINH CITY
HO CHI MINH UNIVERSITY OF TECHNOLOGY**



ASSIGNMENT REPORT IC DESIGN – EE3165

LAB 2 : DIGITAL LOGIC CIRCUIT

CLASS L04 – GROUP 14

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Ho Chi Minh City, May 2024

OBJECTIVES

No.	Objective	Requirement
1	Implement logic gates using CMOS technology: <ul style="list-style-type: none"> ➤ NAND2 and NOR2. ➤ EX-OR2. 	<ul style="list-style-type: none"> ▪ Complete the truth table, schematic, and symbol for each component.
2	Implement basic combinational component: <ul style="list-style-type: none"> ➤ 2-to-1 channel multiplexer. 	<ul style="list-style-type: none"> ▪ Run DC analysis and transient simulation. ▪ Create layouts for each logic gate, then show DRC confirmation and corresponding schematic with proof of LVS.
3	Implement simple storage elements: <ul style="list-style-type: none"> ➤ Single-positive-edge-triggered Modified TSPC D flip-flop. 	<ul style="list-style-type: none"> ▪ Demonstrate latch and flip-flop by studying a D latch and a D flip-flop using transmission gates. ▪ Complete the truth table, schematic, and symbol for each component then run transient simulation. ▪ Known definitions, and how to measure setup time, propagation, and hold time. ▪ Find the clock frequency of this element.
4	[OPTIONAL] Review the operation of pass transistor, transmission gate, and tristate inverter.	<ul style="list-style-type: none"> ▪ Analyze the charge and discharge period of MOS transistors, then prove by simulation. ▪ Analyze operations of a transmission gate, then prove by simulation. ▪ Analyze operations and topologies of a tristate inverter, then prove by simulation.

EXPERIMENT 1 : Know how to design CMOS gate using CMOS technology.

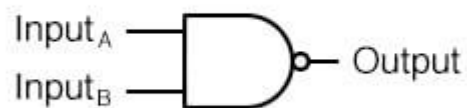
Requirements :

- Complete truth table, schematic, and symbol for NAND2, NOR2, and EX-OR2
- Run DC simulation and transient analysis
- Create layout and show DRC and LVS check screen

1. NAND2

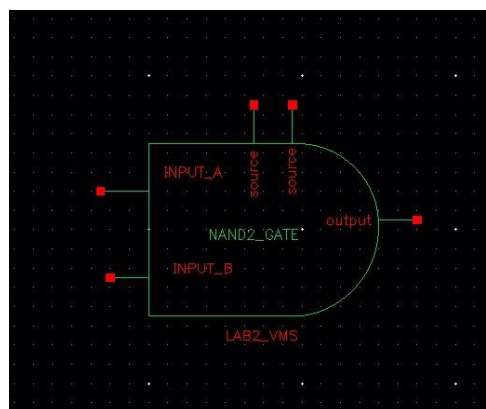
The truth table of NAND2 gate and its symbol

2 - input NAND gate

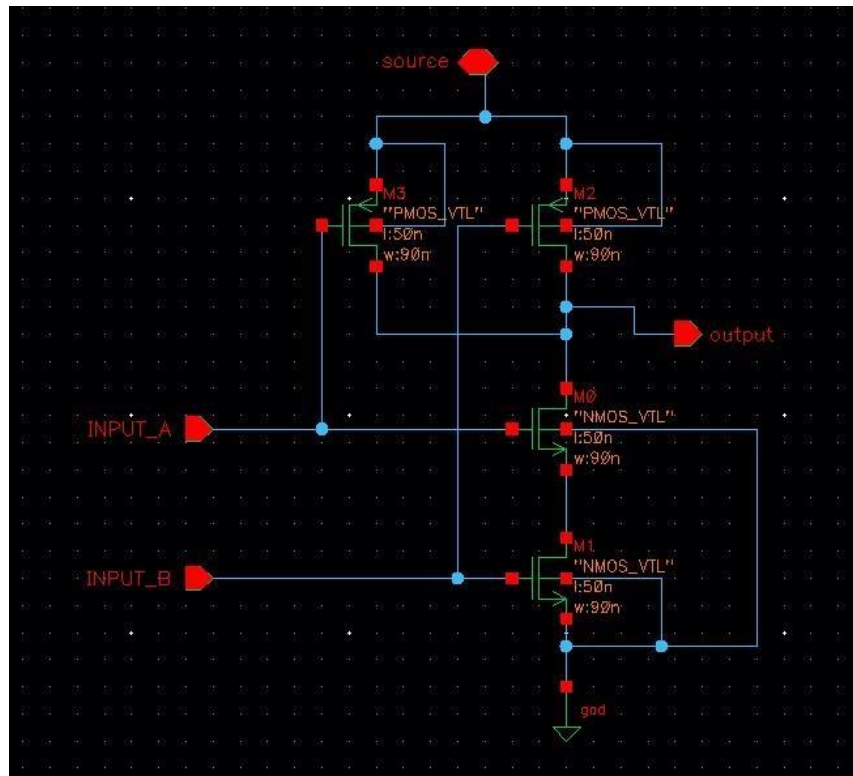


A	B	Output
0	0	1
0	1	1
1	0	1
1	1	0

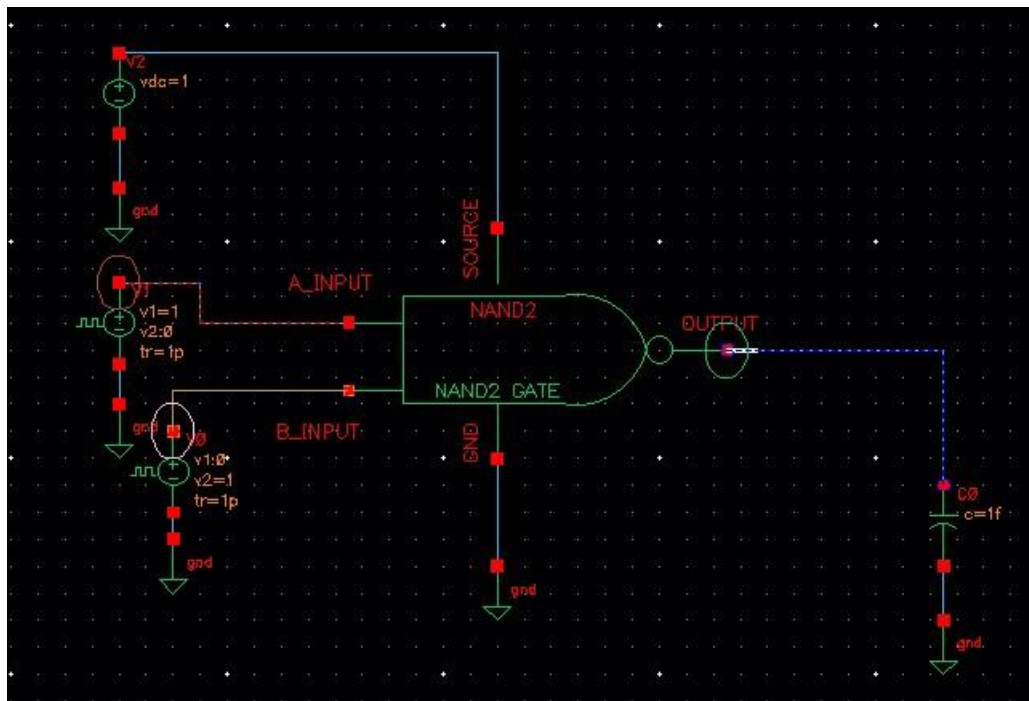
Firstly, I create NAND2 symbol but my symbol is lack of circle.

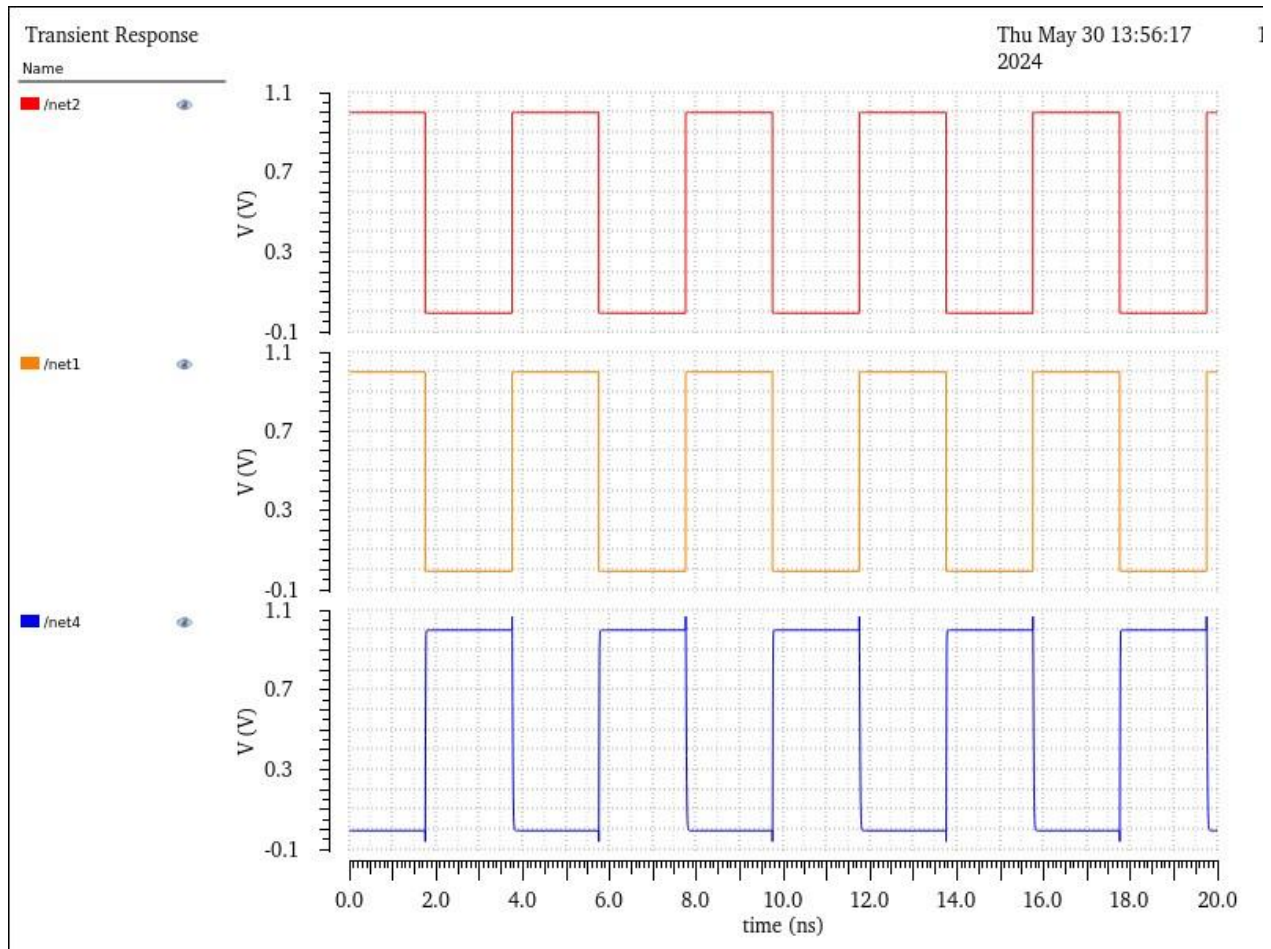


NAND2 schematic



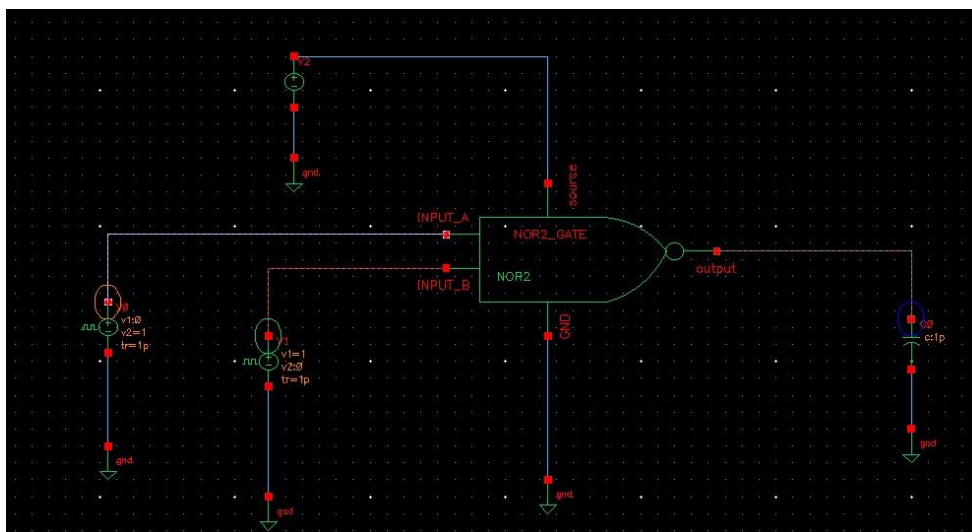
My testbench is designed as



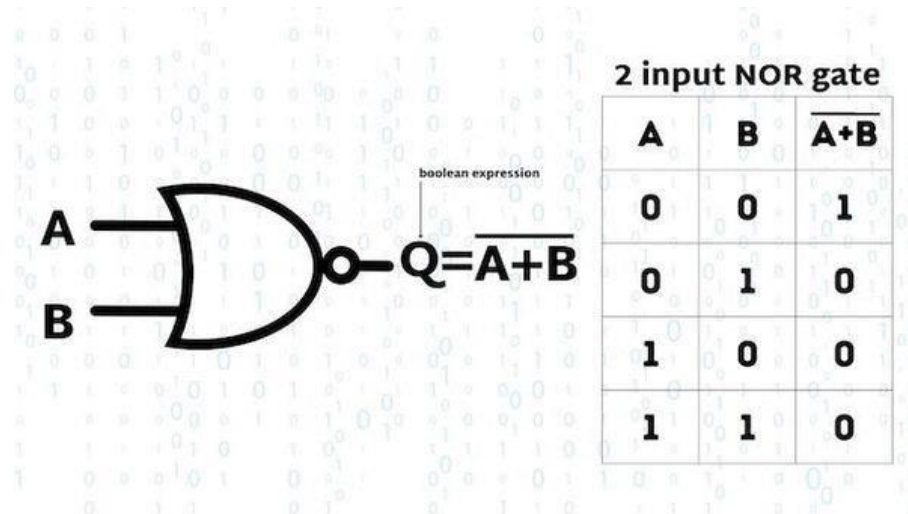


Transient simulation with 20n s 2.

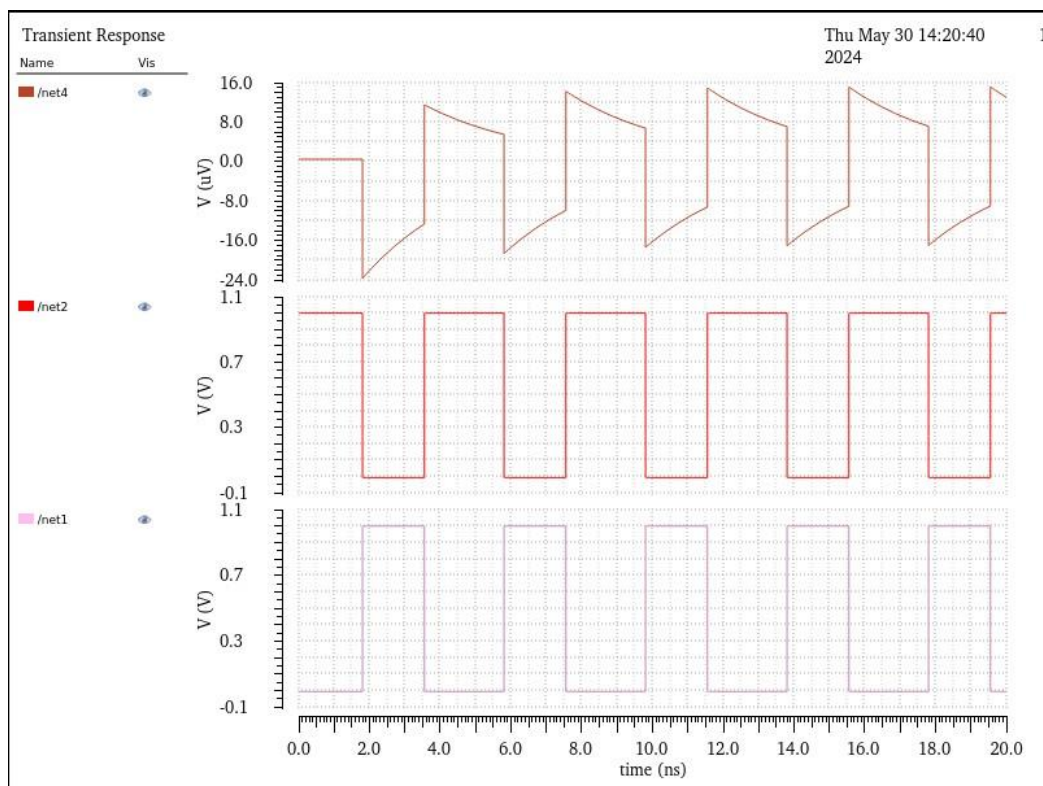
NOR2



Here is my schematic and testbench for NOR2 the symbol is created as the figure below. And the testbench included 2 pulse source and a Vdc source.



The simulation is showed with the transient of 20n s.



The plot is not perfectly the pulse source because of the setting is as the figure below :

CDF Parameter	Value	Display
Frequency name for 1/period		off
Noise file name		off
Number of noise/freq pairs	0	off
DC voltage		off
AC magnitude		off
AC phase		off
XF magnitude		off
PAC magnitude		off
PAC phase		off
Voltage 1	0 V	off
Voltage 2	1 V	off
Period	4n s	off
Delay time	1.8n s	off
Rise time	1p s	off
Fall time	1p s	off
Pulse width	1.75n s	off
Temperature coefficient 1		off
Temperature coefficient 2		off
Nominal temperature		off

This is the vpulse of the input B

PAC magnitude		off
PAC phase		off
Voltage 1	1 V	off
Voltage 2	0 V	off
Period	4n s	off
Delay time	1.8n s	off
Rise time	1p s	off
Fall time	1p s	off
Pulse width	1.75n s	off
Temperature coefficient 1		off
Temperature coefficient 2		off
Nominal temperature		off

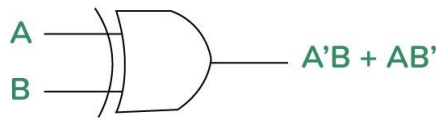
This is the vpulse of the input A

3. EX-OR

The figure below shows the EX-OR truth table and its symbol. As the theory, EXOR is created by 2 input A and B. And a AND gate and NOR gate.

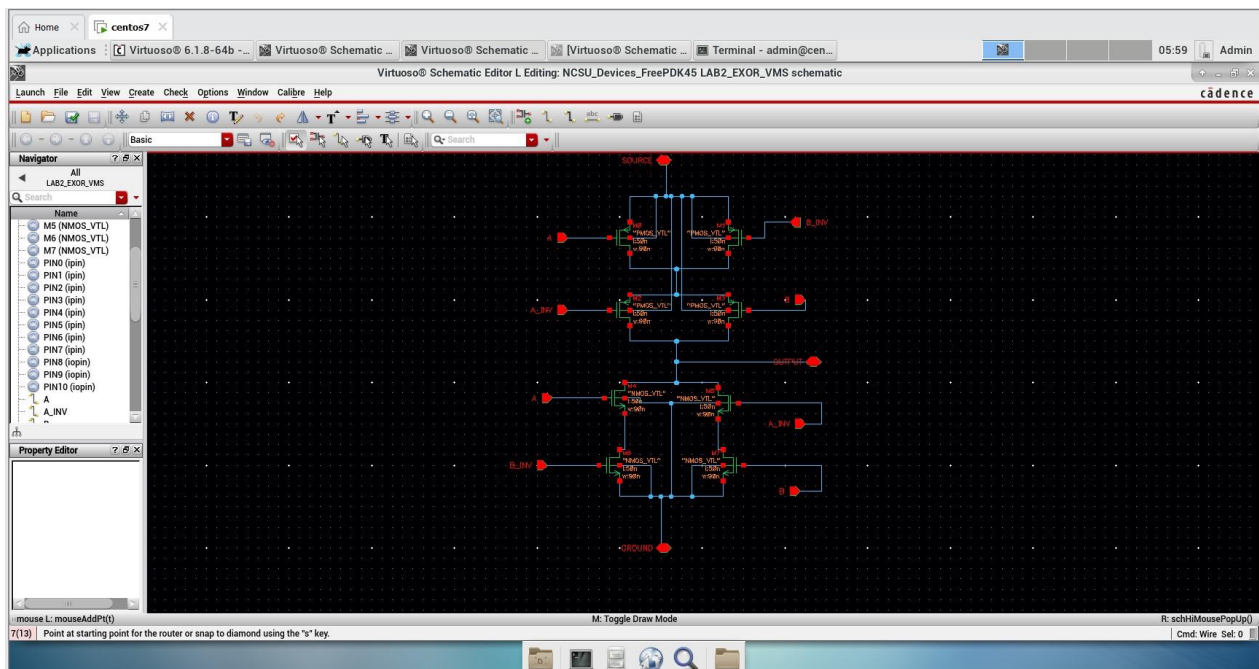
For creating EX-OR, I simulate by schematic of CMOS gate with an inverter of each inputs. By the way, we can create by using NAND2 and NOR2 gate before.

XOR Gate



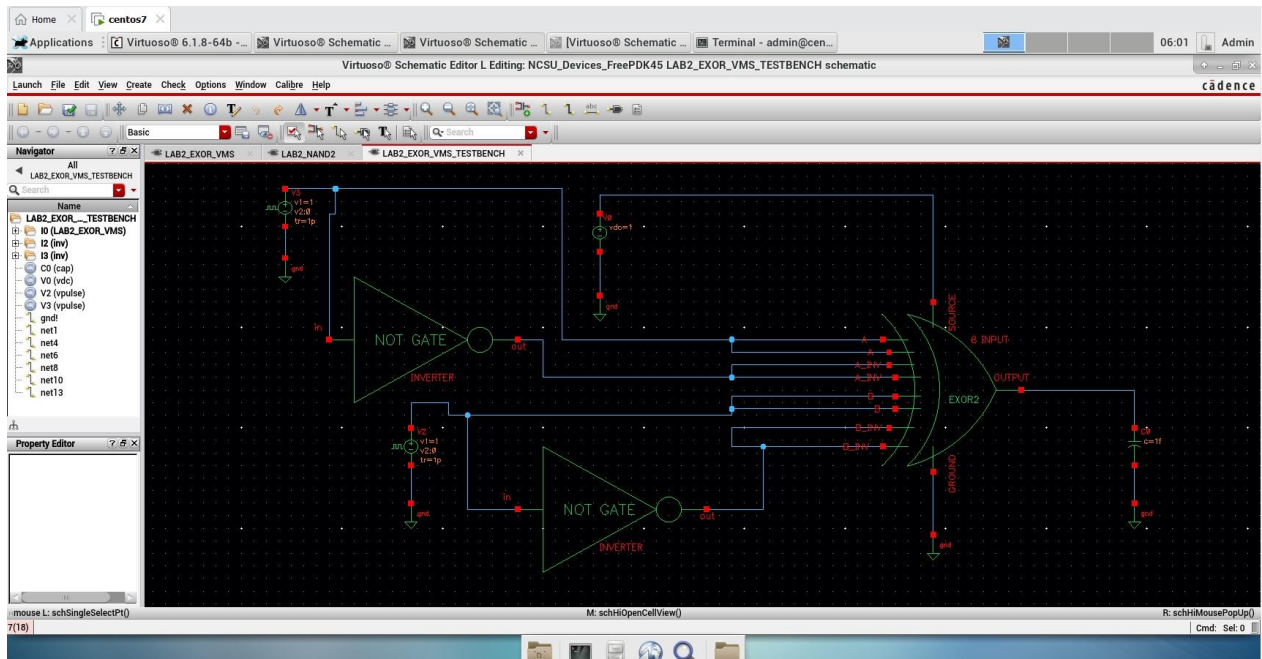
Truth Table

A (Input 1)	B (Input 2)	X = A'B + AB'
0	0	0
0	1	1
1	0	1
1	1	0

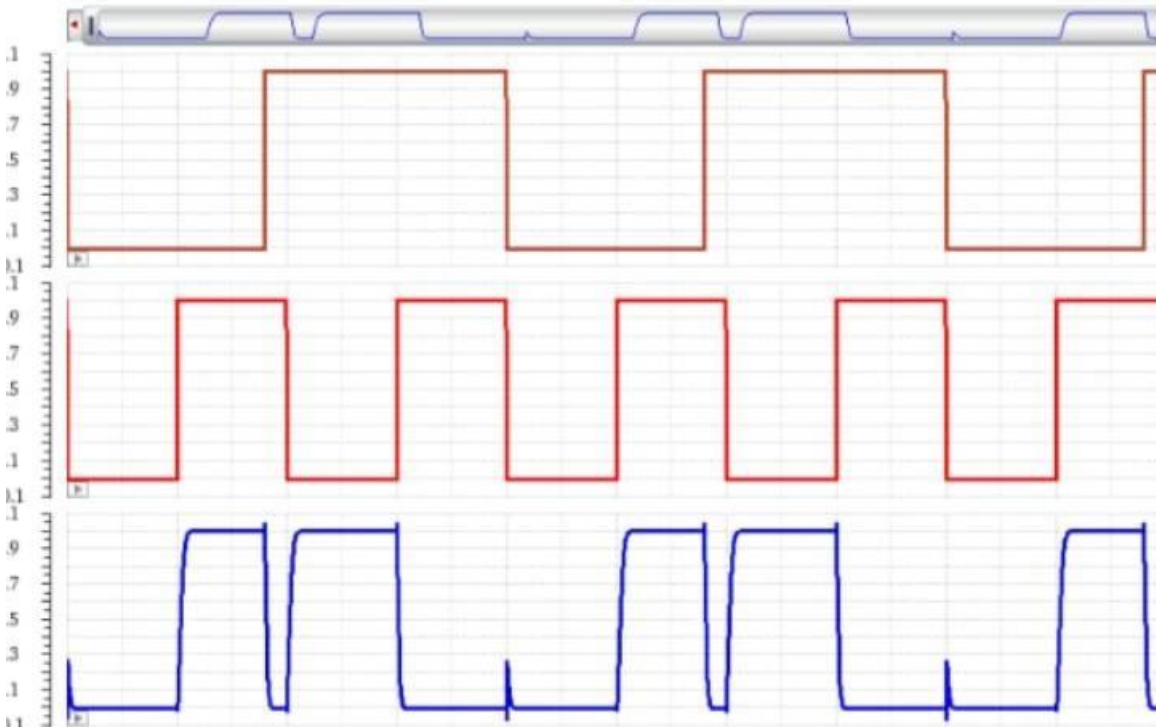


The schematic of EX-OR gate

I used compound gate theory to create this schematic with 4 inputs. But we need an inverter for creating this gate. So that the symbol I create for simulation included 4 inputs.



The result of the simulation is showed as below.



I deleted the current state of the simulation tools, the result shows that the edge rising directly affected to the wave.

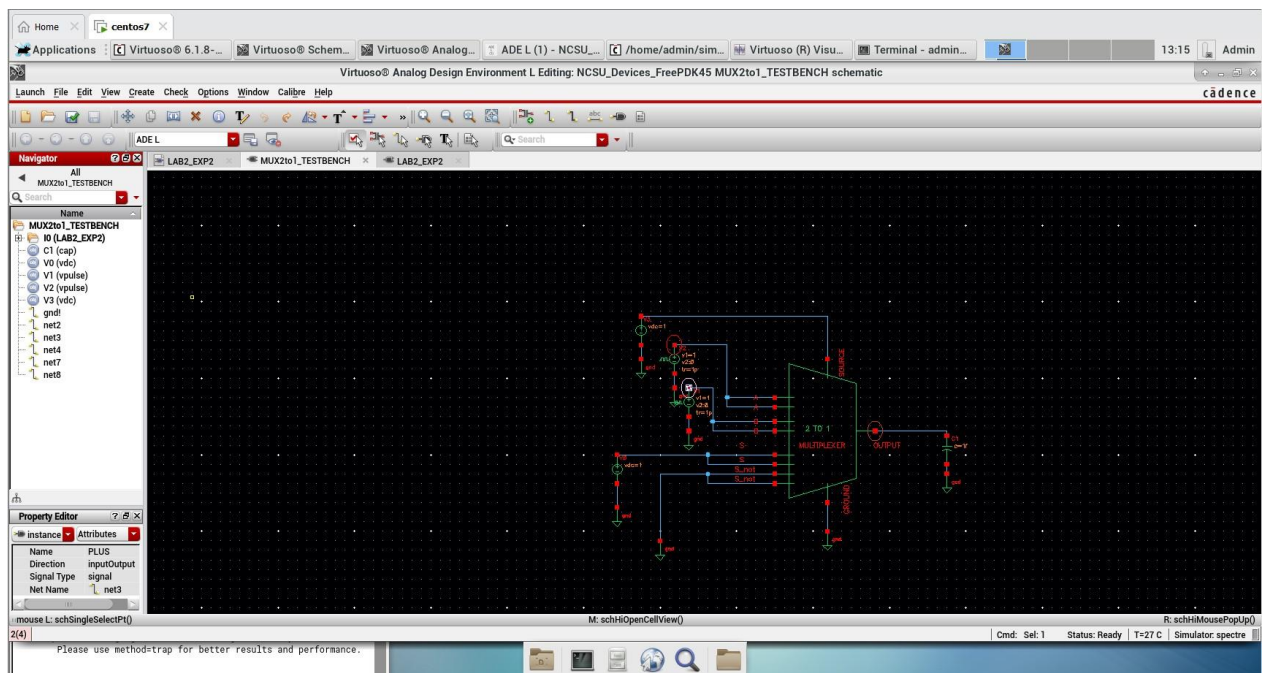
$V_{in1}(V)$	0.1	0.2	0.3	0.4	0.5	0.6	0.7	0.8	0.9	1.0
$V_{in2}(V)$	0.1	0.2	0.3	0.4	0.5	0.6	0.7	0.8	0.9	1.0
V_{out}	999mV	996.3mV	971.2mV	398.2mV	29mV	999mV	999mV	999mV	999mV	999mV

EXPERIMENT 2 : Implement basic combinational component.

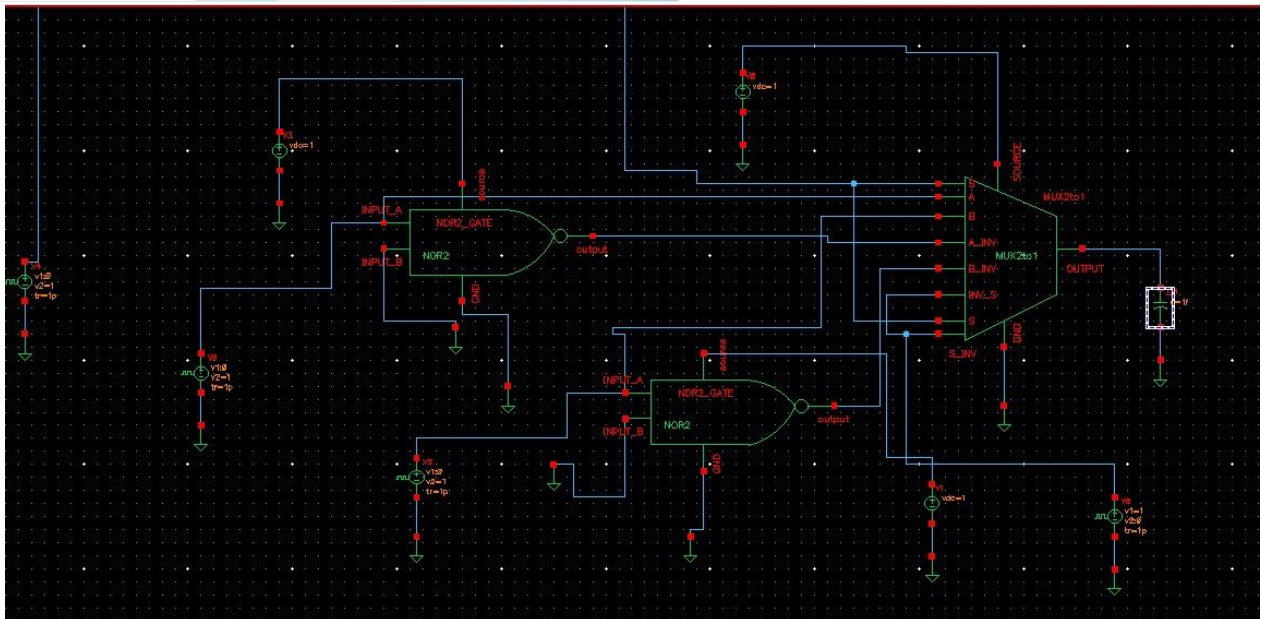
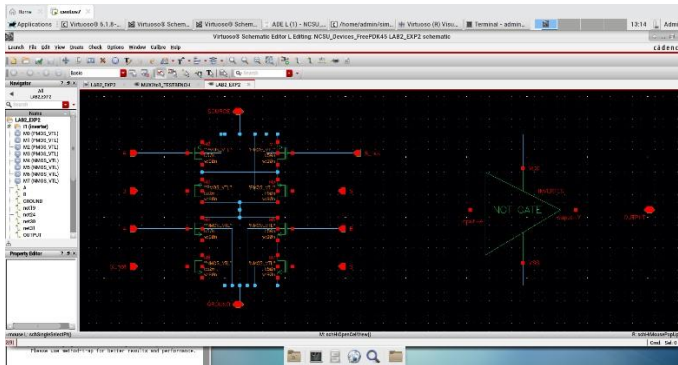
Requirements:

- Complete the truth table, schematic, and symbol for a 2-to-1 channel multiplexer using compound gate.
- Run DC analysis and transient simulation.
- Create layouts for each logic gate, then show DRC confirmation and corresponding schematic with proof of LVS.

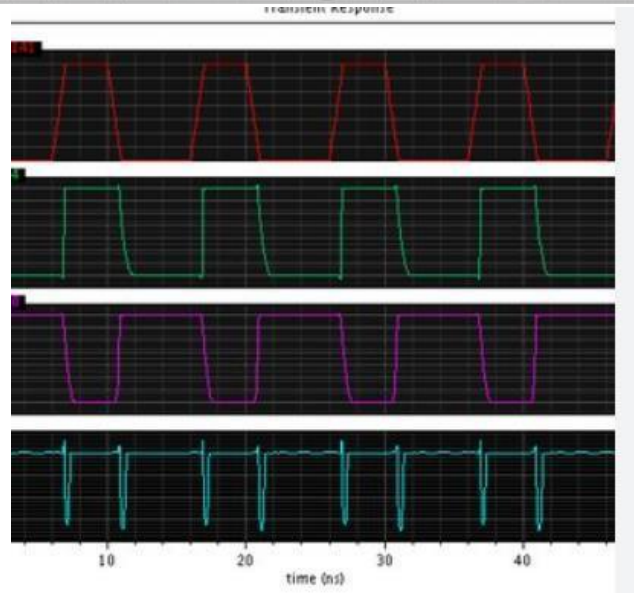
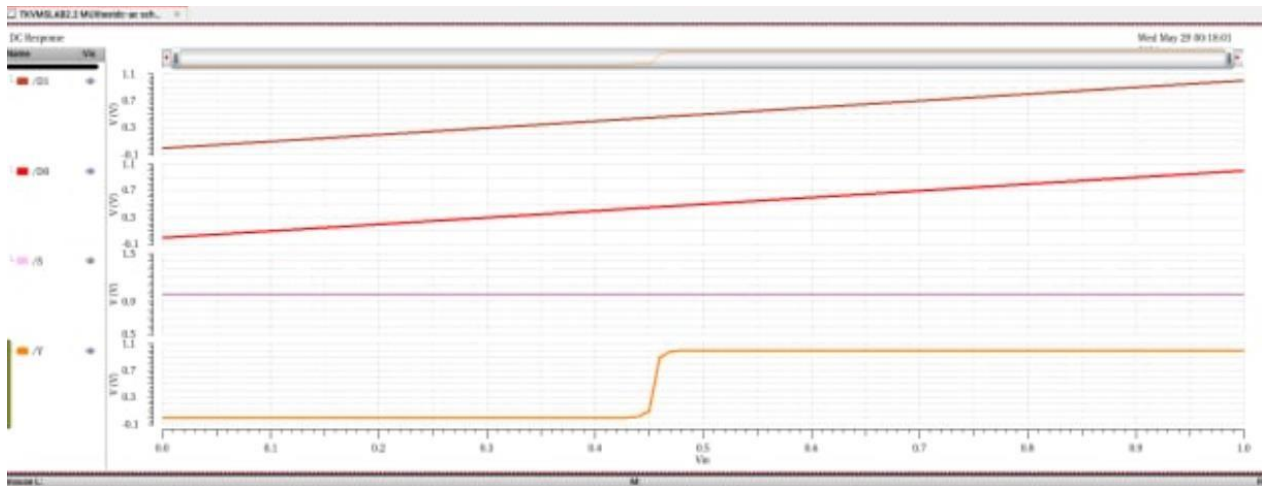
My multiplexers



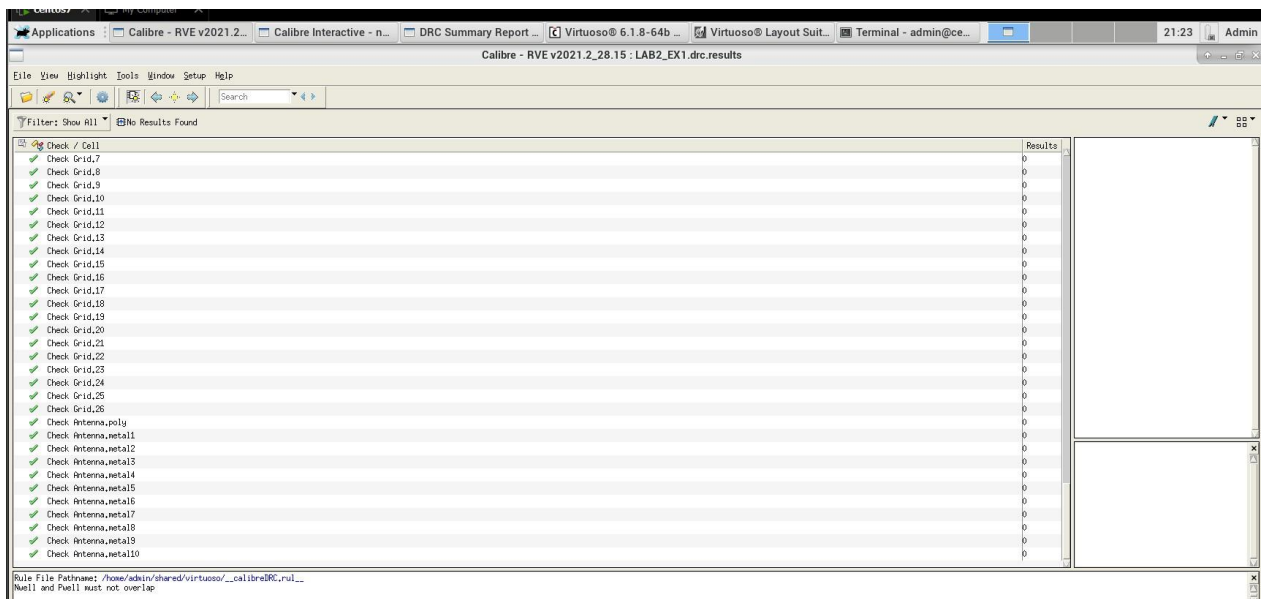
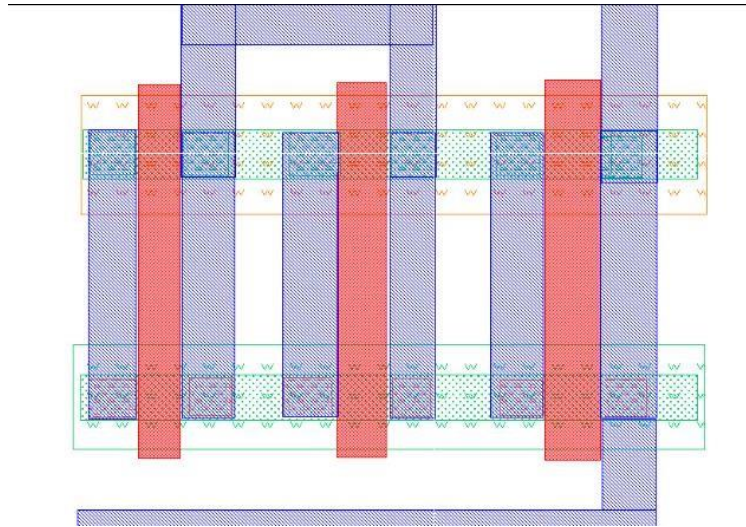
I used MUX2 to 1 as the schematic above with the testbench My schematic is



DC simulation



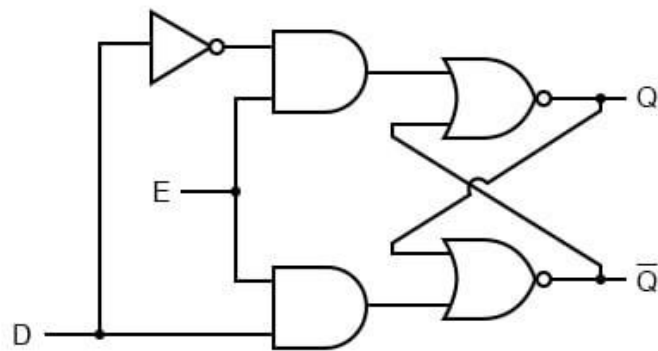
	S	D0	D1
V1	0	0	0
V2	1	1	1
Period	4n	3n	2n
Delay time	0	0	0
Rise time	1p	1p	1p
Fall time	1p	1p	1p
Pulse width	2n	1.5n	1n



DRC check

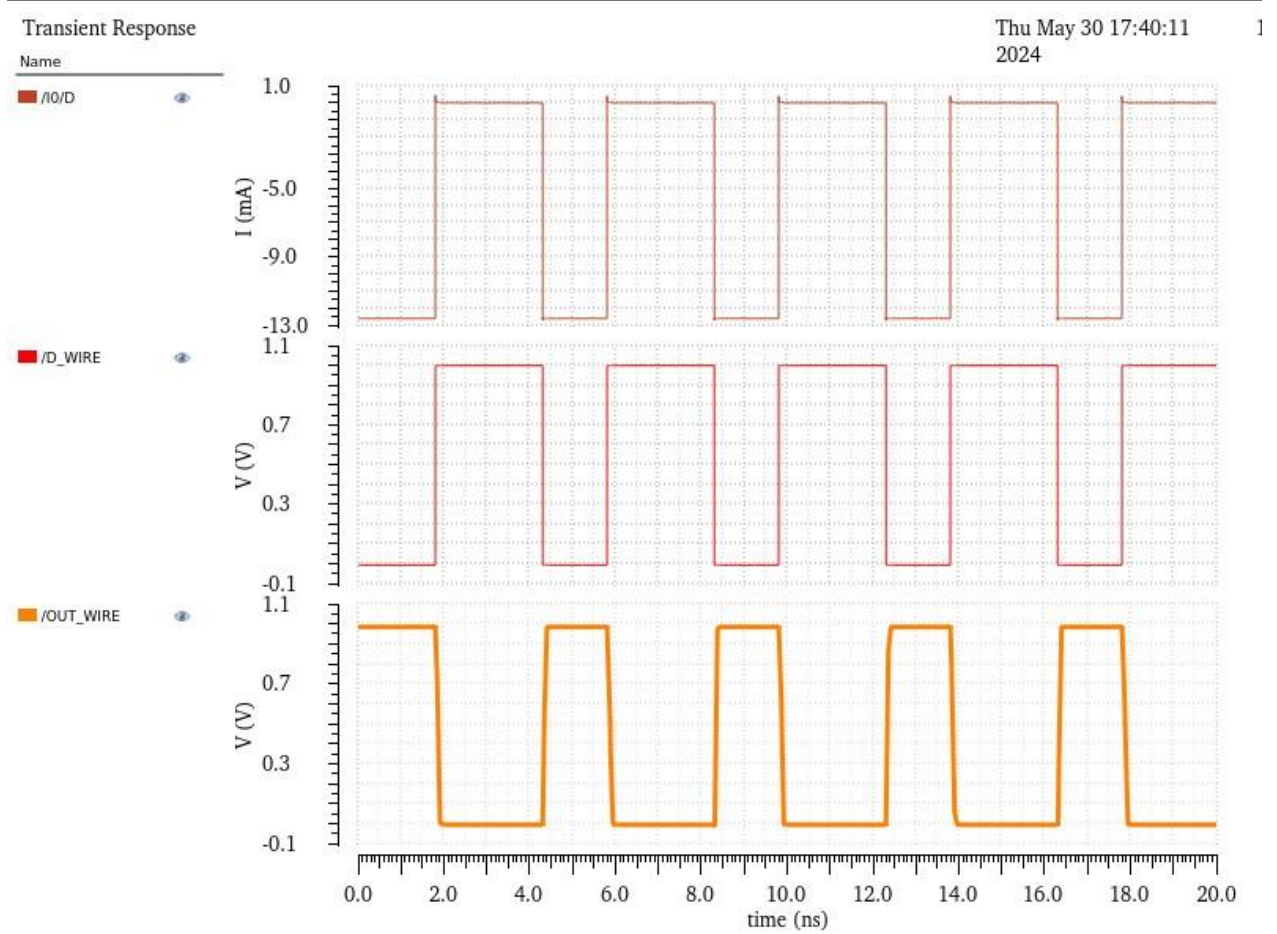
EXPERIMENT 3 : Implementing simple storage elements- single-positive – edge triggered Modified TSPC D flip-flop.

Latch D demonstration

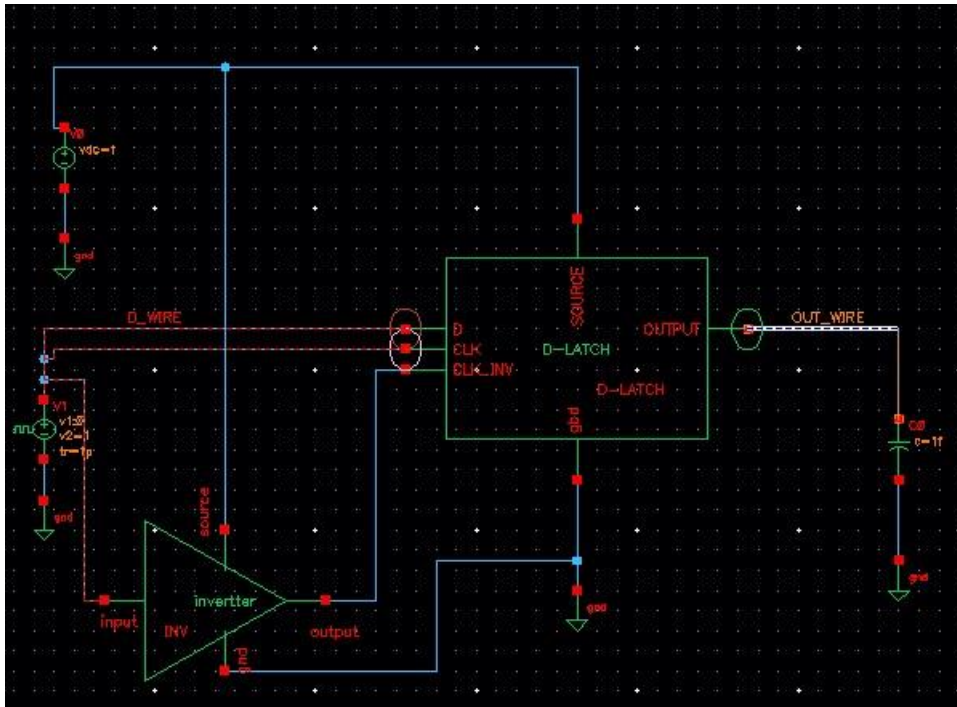


E	D	Q	\bar{Q}
0	0	latch	latch
0	1	latch	latch
1	0	0	1
1	1	1	0

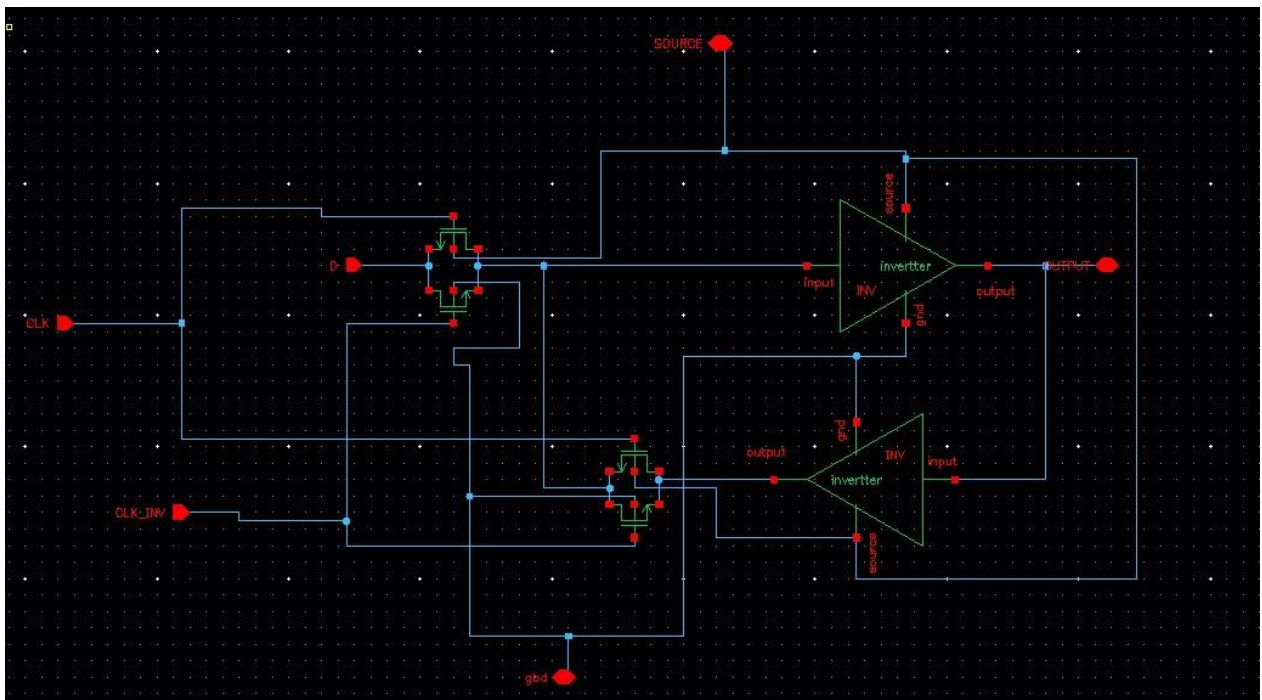
D-latch truth table



D-Latch simulation in trans 20n

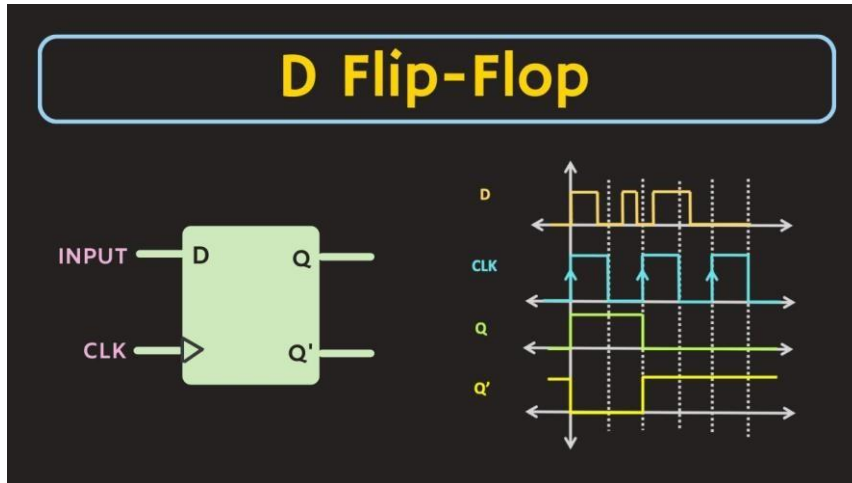


Testbench schematic



D-latch schematic

D – FLIP FLOP



Truth table and symbol

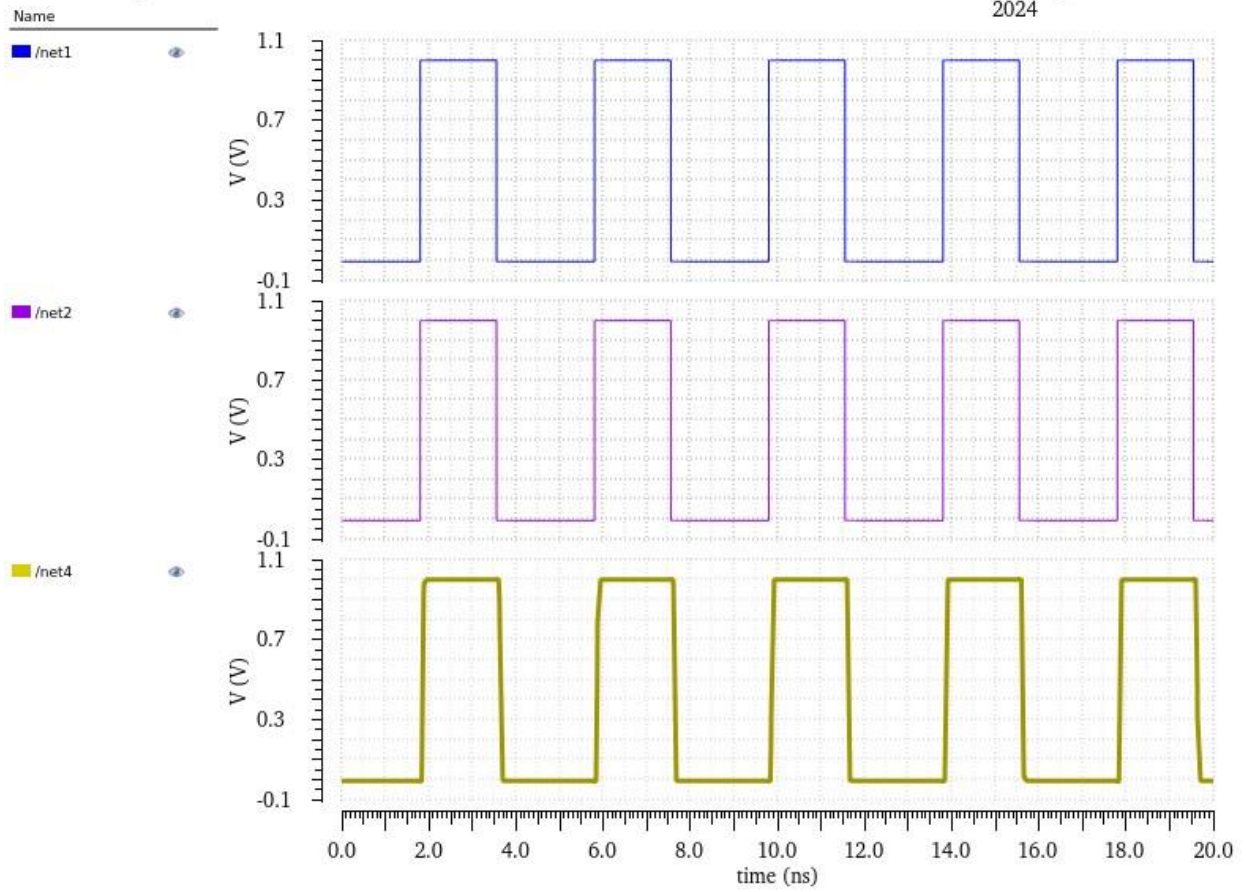
$\overline{\text{SET}}$	$\overline{\text{RESET}}$	D	CK	Q	$\overline{\text{Q}}$
0	1	-	-	1	0
1	0	-	-	0	1
0	0	-	-	1	1
1	1	1		1	0
1	1	0		0	1

Transient response

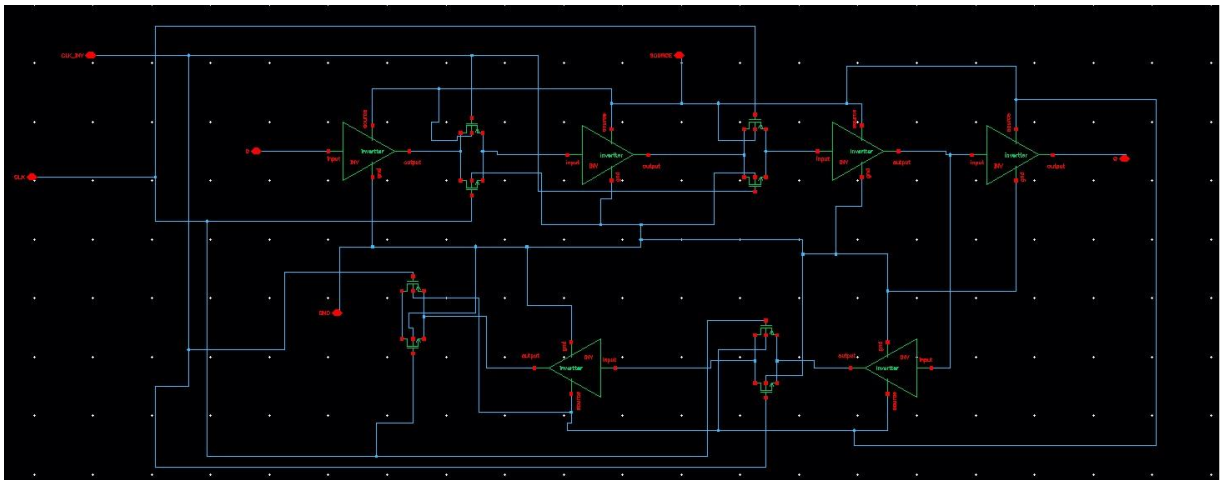
Transient Response

Thu May 30 18:11:29
2024

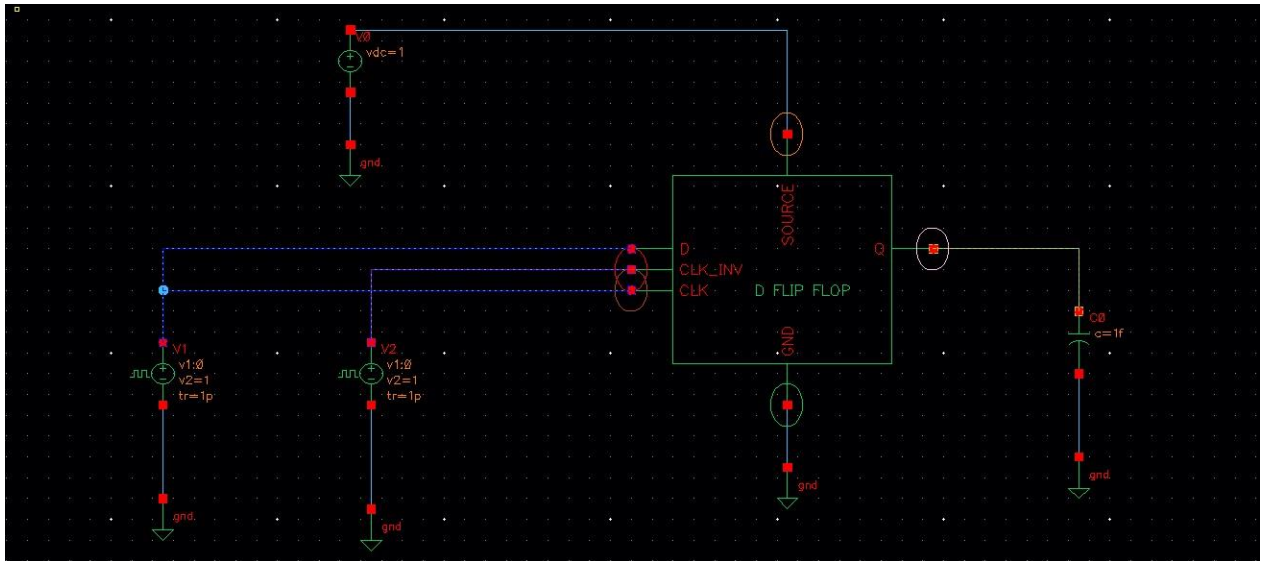
1



SCHEMATIC



TESTBENCH



Clock configuration

virtuoso® Analog Des... [ADE L (4) - NCSU_Dev... Edit Object Properties

Edit Object Properties

View Name: symbol off

Instance Name: V0 off

User Property: Add Delete Modify

Master Value: Local Value: Display

Ignore: TRUE off

CDF Parameter

Parameter	Value	Display
Frequency name for 1/period		off
Noise file name		off
Number of noise/freq pairs	0	off
DC voltage		off
AC magnitude		off
AC phase		off
XF magnitude		off
PAC magnitude		off
PAC phase		off
Voltage 1	0 V	off
Voltage 2	1	off
Period	4n s	off
Delay time	1.75n s	off
Rise time	1p s	off
Fall time	1p s	off
Pulse width	1.8n s	off
Temperature coefficient 1		off
Temperature coefficient 2		off
Nominal temperature		off
Type of rising & falling edge		off

OK Cancel Apply Defaults Previous Next Help

Parameters	Results
t_{pd}	0.0644(ns)
t_{cd}	0.029(ns)
t_{pcq}	0.0306(ns)
t_{ccq}	0.0219(ns)
t_{setup}	0.05312(ns)
t_{hold}	14.521pW